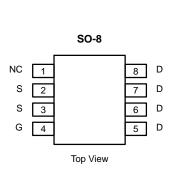
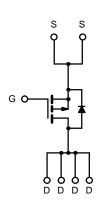


# P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	
-20	0.25 @ V <sub>GS</sub> = -10 V	± 2.5	
	0.40 @ V <sub>GS</sub> = -4.5 V	±2.0	





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Limit	Unit					
Drain-Source Voltage		V <sub>DS</sub>	-20	V				
Gate-Source Voltage		$V_{GS}$	±20	'				
Continuous Drain Current (T,I = 150°C) <sup>a</sup>	T <sub>A</sub> = 25°C	ı	± 2.5					
Continuous Diam Current (1) = 150 C)-	T <sub>A</sub> = 70°C	'D	±2.0	]				
Pulsed Drain Current		I <sub>DM</sub>	±10	1 ^				
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	-2.0	1				
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25°C	Pn	2.5	w				
IMAXIIIIUIII FUWEI DISSIPAUUII-	T <sub>A</sub> = 70°C	FD -	1.6	<b>**</b>				
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C				

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	50	°C/W		

### Notes

a. Surface Mounted on FR4 Board,  $t \le 10$  sec.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

# **Si9400DY**

# **Vishay Siliconix**



SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Тура	Max	Unit	
Static			-				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-1.0			٧	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana l	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-2	μΑ	
Zero Gale vollage Drain Current	DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10			Α	
Drain-Source On-State Resistance <sup>b</sup>	fac: :	$V_{GS} = -10 \text{ V}, I_D = 1 \text{ A}$		0.13	0.25	Ω	
Diami-Source Oir-State Resistance	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = 0.5 \text{ A}$		0.22	0.40		
Forward Transconductance <sup>b</sup>	9fs	$V_{DS} = -15 \text{ V}, I_D = -2.5 \text{ A}$		2.5		S	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	$I_S = -1.25 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8	-1.6	٧	
Dynamic <sup>a</sup>							
Total Gate Charge	Qg			6.8	25	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10$ V, $V_{GS} = -10$ V, $I_D = -2.0$ A		1.3			
Gate-Drain Charge	$Q_{gd}$			1.6			
Turn-On Delay Time	t <sub>d(on)</sub>			10	40	ns	
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6 \Omega$		12	40		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -1 \overline{A}$ , $V_{GEN} = -10 V$ , $R_G = 6 \Omega$		20	90		
Fall Time	t <sub>f</sub>			10	50		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2 A, di/dt = 100 A/μs	<u> </u>	69	100	1	

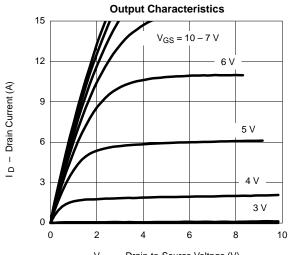
Notes a. For design aid only; not subject to production testing.

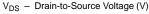
b. Pulse test; pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ .

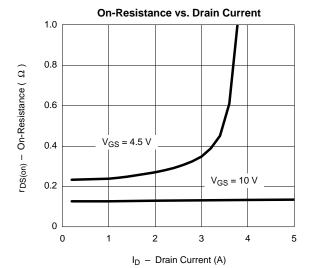




## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)







VGS - Gate-to-Source Voltage (V) 6 2 0

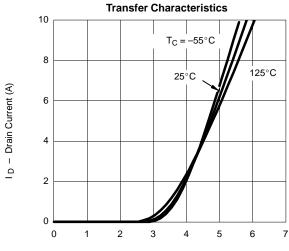
V<sub>DS</sub> =10 V

 $I_D = 2 A$ 

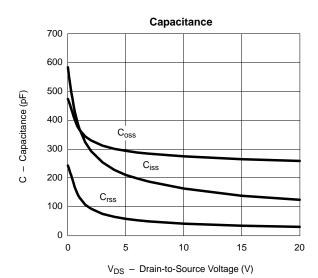
Q<sub>g</sub> - Total Gate Charge (nC)

8

**Gate Charge** 



V<sub>GS</sub> - Gate-to-Source Voltage (V)



On-Resistance vs. Junction Temperature 2.0 1.6  $V_{GS} = 10 \text{ V}$  $I_D = 1.0 \text{ A}$ r  $\mathrm{DS}(\mathrm{on})-$  On-Resistance (  $\Omega$  ) (Normalized) 1.2 0.8 0.4 -50 -25 0 25 75

 $T_J$  – Junction Temperature (°C)

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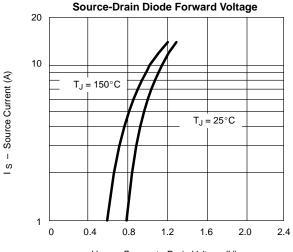
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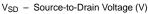
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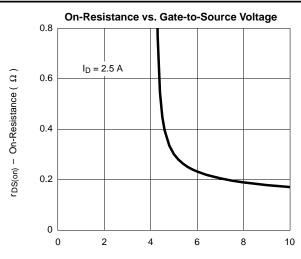
# **Vishay Siliconix**



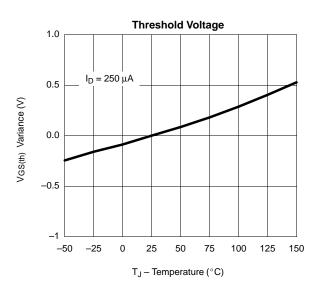
## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

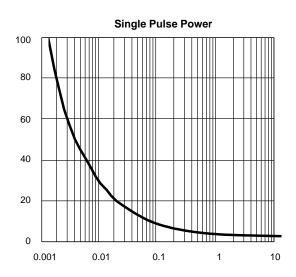


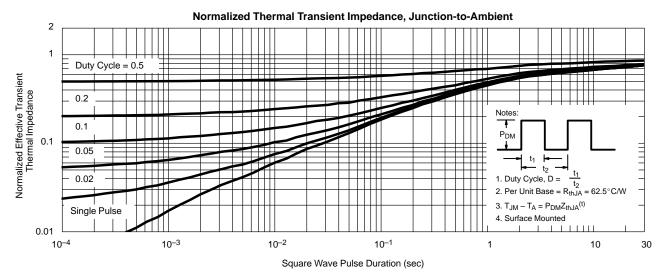




V<sub>GS</sub> – Gate-to-Source Voltage (V)









Vishay

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